

Features

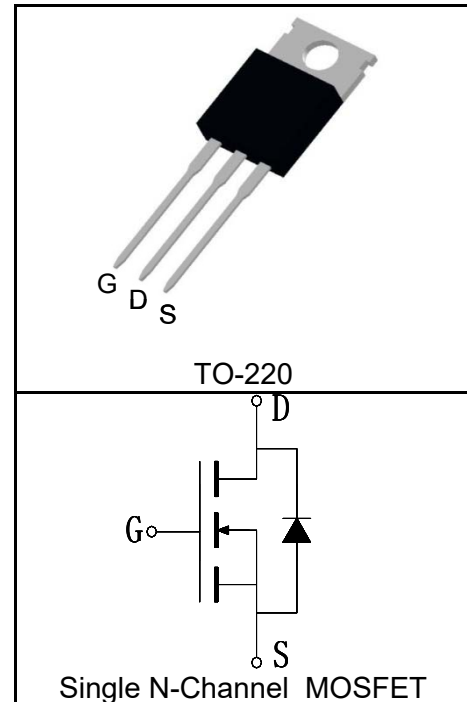
- 100V/130A,
 $R_{DS(ON)} = 6.7m\Omega(Typ.)@V_{GS}=10V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged
- 100% Avalanche Tested

Applications

- DC-DC Converters and Off-line UPS
- Power Management in Inverter System



Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	130	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _C =25°C	520	A
I _D ^②	Continuous Drain Current(V _{GS} =10V)	T _C =25°C	130	A
		T _C =100°C	92	
P _D	Maximum Power Dissipation	T _C =25°C	230	W
		T _C =100°C	115	
R _{θJC}	Thermal Resistance-Junction to Case		0.65	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		62.5	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		900	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

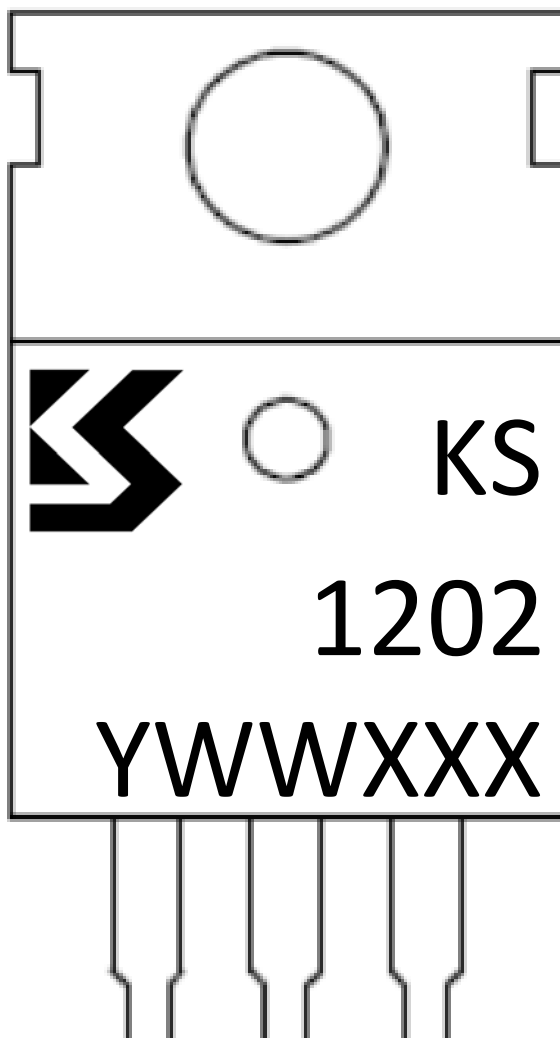
Symbol	Parameter	Test Condition	KS1202CC			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V			1	μA
			T _J =125°C			
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2		4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =40A		6.7	8	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =40A, V _{GS} =0V		0.84	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =40A, dI _{SD} /dt=100A/μs		28		ns
Q _{rr}	Reverse Recovery Charge			110		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		3.2		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, Frequency=1.0MHz		4090		pF
C _{oss}	Output Capacitance			470		
C _{rss}	Reverse Transfer Capacitance			310		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =50V, I _{DS} =40A, V _{GEN} =10V, R _G =3Ω		28		ns
t _r	Turn-on Rise Time			60		
t _{d(OFF)}	Turn-off Delay Time			86		
t _f	Turn-off Fall Time			23		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _{DS} =40A		69		nC
Q _{gs}	Gate-Source Charge			23		
Q _{gd}	Gate-Drain Charge			22		

Notes:

- ① Pulse width limited by safe operating area.
- ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
- ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
- ④ Limited by T_{Jmax} , $I_{AS}=60A$, $L=0.5\text{mH}$, $V_{DD}=48V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$.
- ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS1202CC	TO-220	Tube	50	-	-

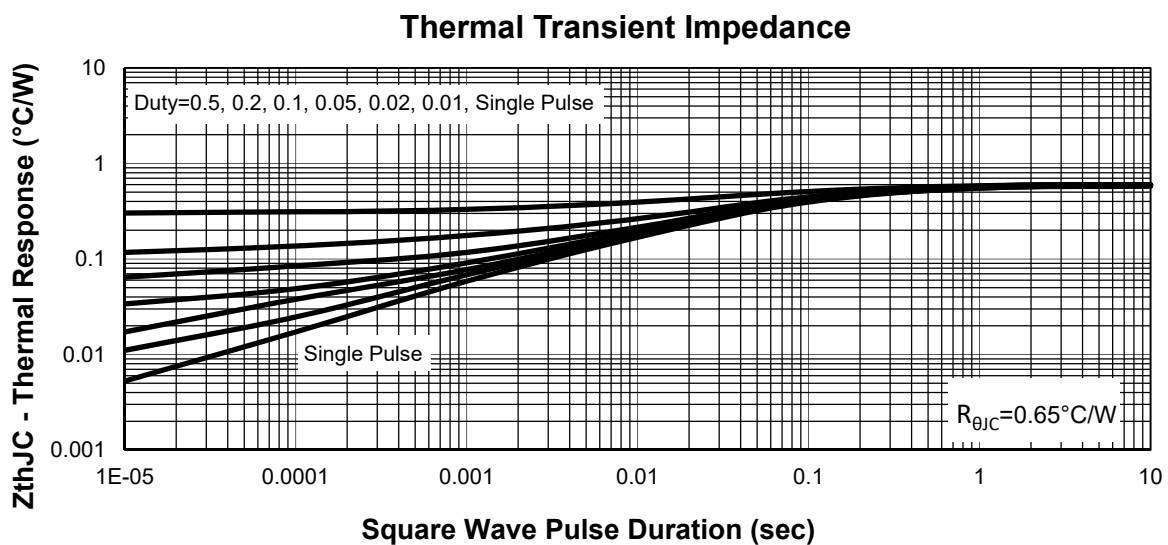
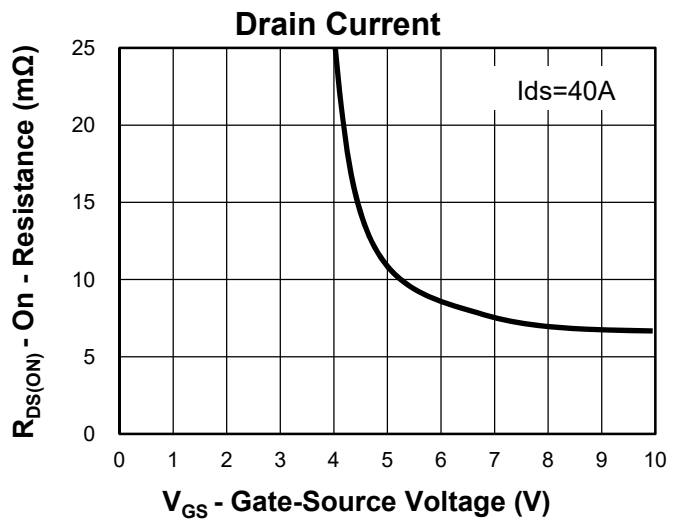
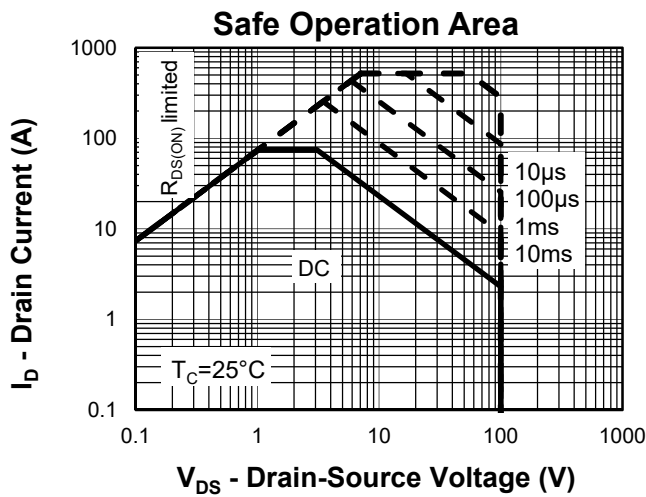
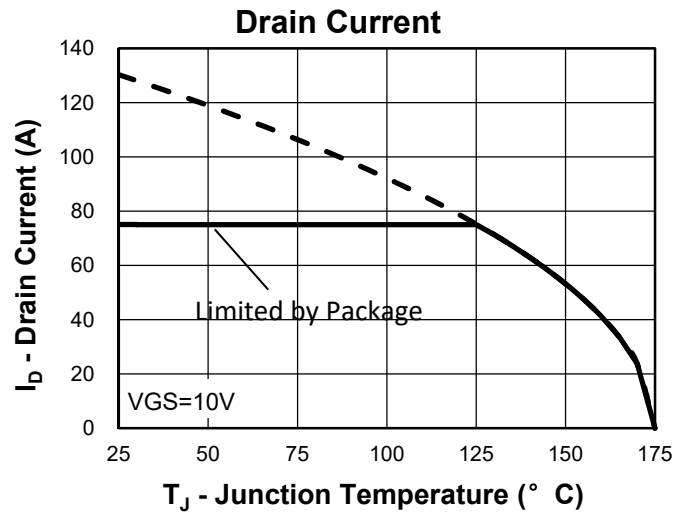
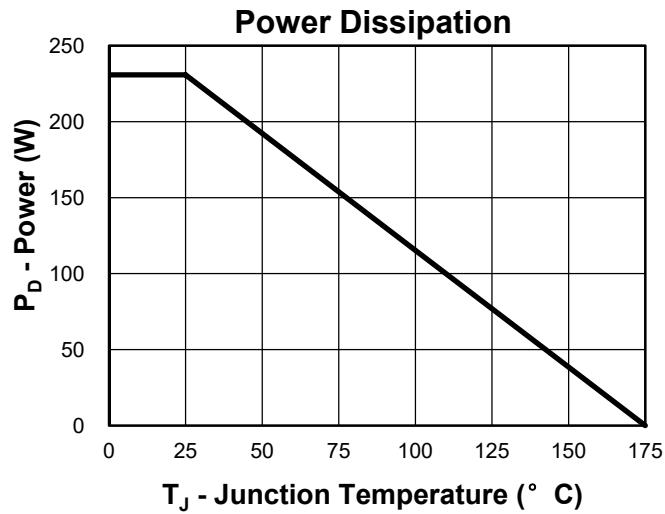


Y =Year,2017-A,2018-B,etc.

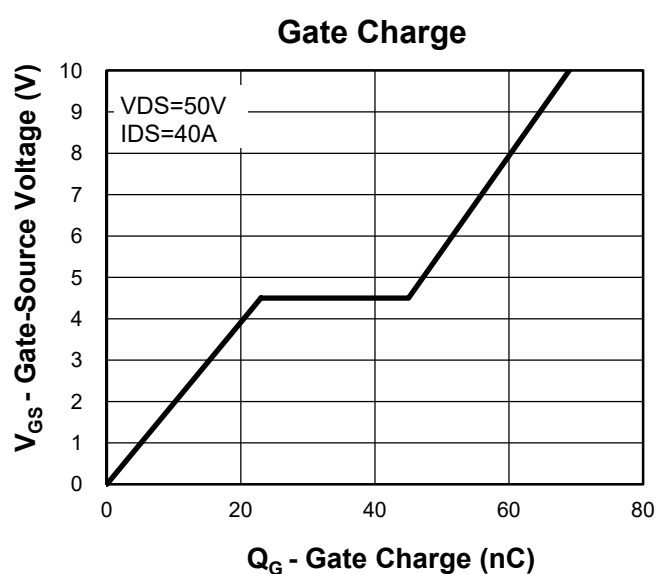
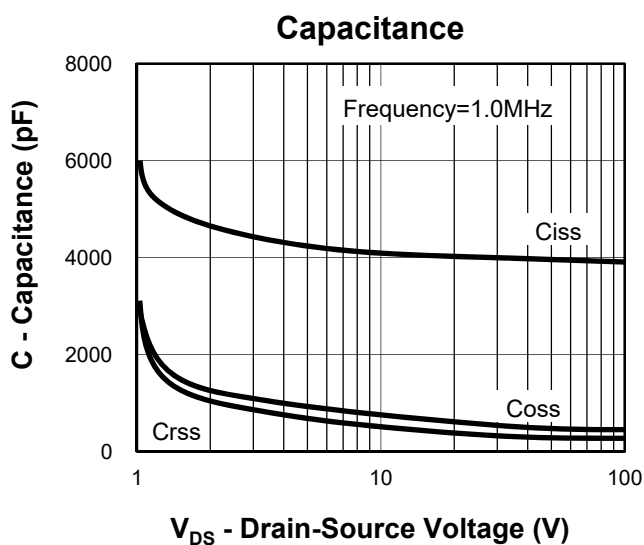
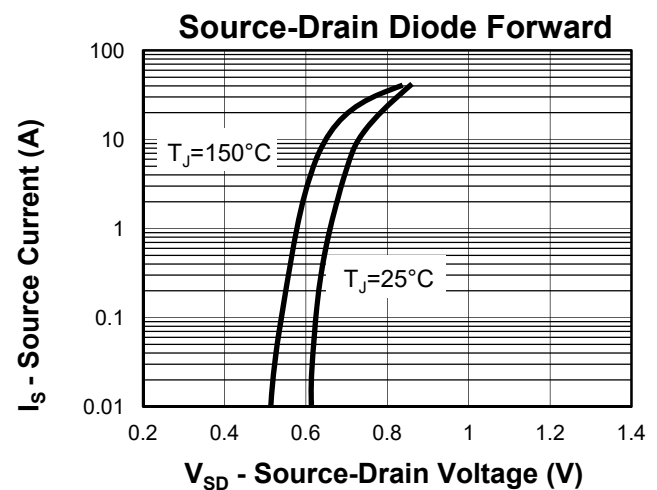
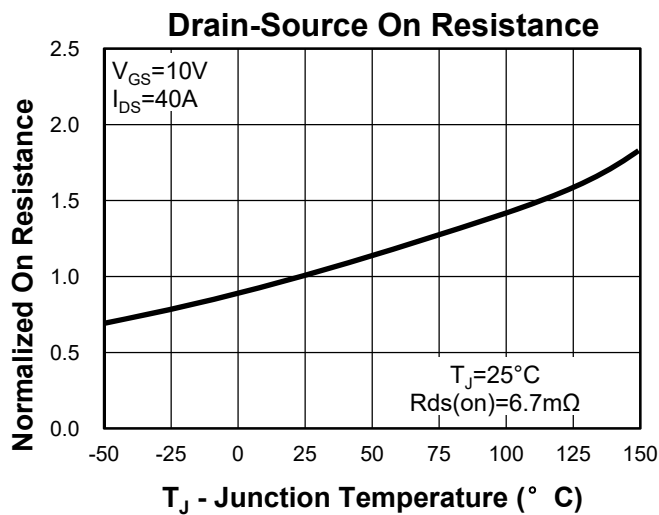
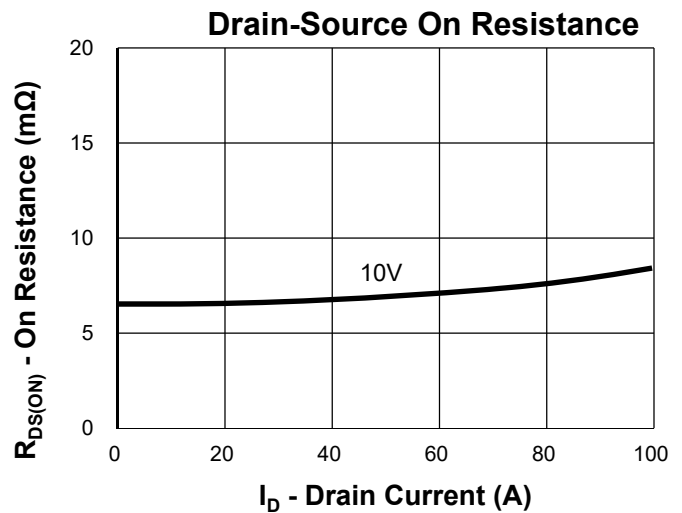
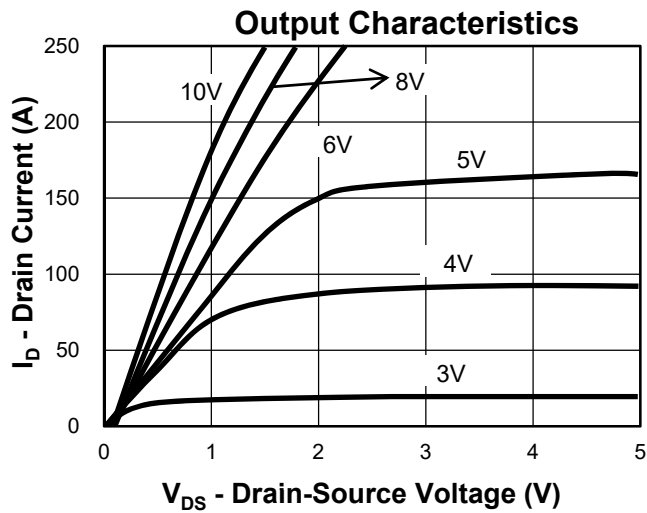
WW =Week.

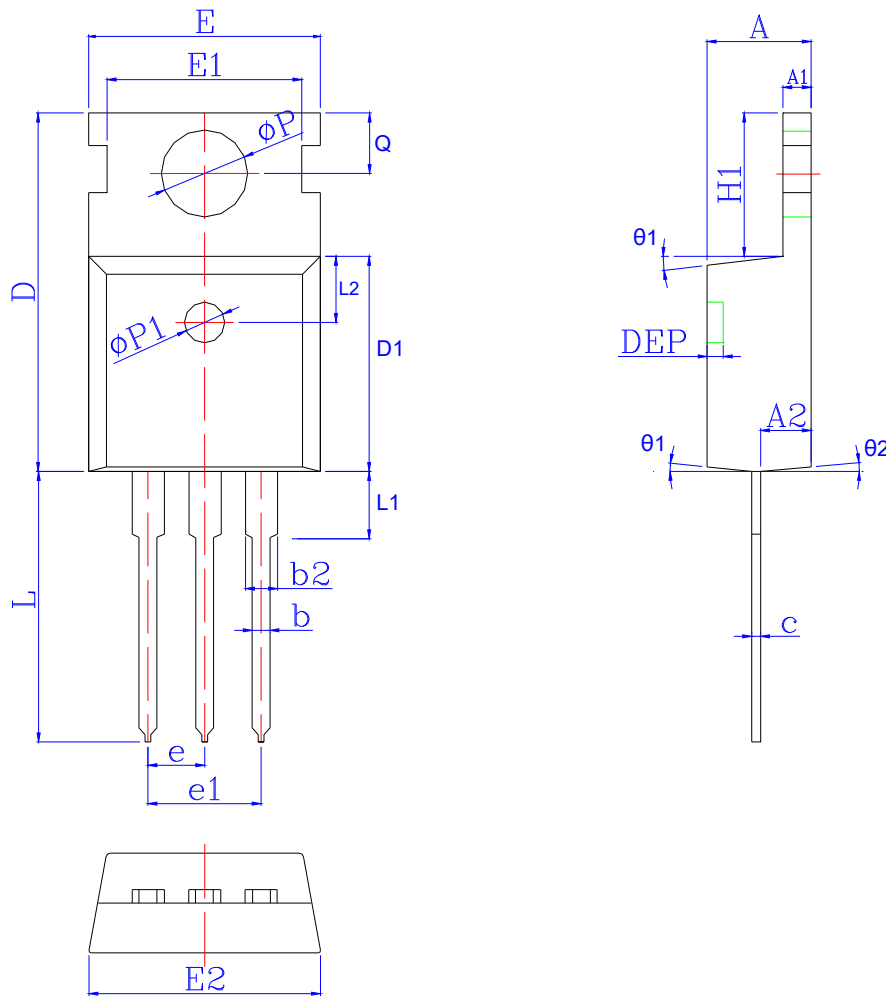
XXX =Lot number.

Typical Characteristics



Typical Characteristics



Package Information
TO-220


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.54	4.77	0.169	0.179	0.188	$\Phi p1$	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.15	1.30	1.40	0.045	0.051	0.055	e	2.54 BSC			0.10 BSC		
A2	1.90	2.25	2.60	0.075	0.089	0.102	e1	5.08 BSC			0.20 BSC		
b	0.60	0.80	1.00	0.024	0.031	0.039	H1	6.30	6.50	6.80	0.248	0.256	0.268
b2	1.17	1.28	1.72	0.046	0.050	0.068	L	12.70	13.18	13.65	0.500	0.519	0.537
c	0.40	0.50	0.60	0.016	0.020	0.024	L1	*	*	3.95	*	*	0.156
D	15.40	15.70	16.00	0.606	0.618	0.630	L2	2.50 REF			0.098 REF		
D1	8.96	9.21	9.46	0.353	0.363	0.372	Φp	3.50	3.60	3.75	0.138	0.142	0.148
DEP	*	*	0.30	*	*	0.012	Q	2.70	2.80	3.20	0.106	0.110	0.126
E	9.66	9.97	10.28	0.380	0.393	0.405	$\theta 1$	5°	7°	9°	5°	7°	9°
E1	*	8.70	*	*	0.343	*	$\theta 2$	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.402							

Avalanche Test Circuit and Waveforms



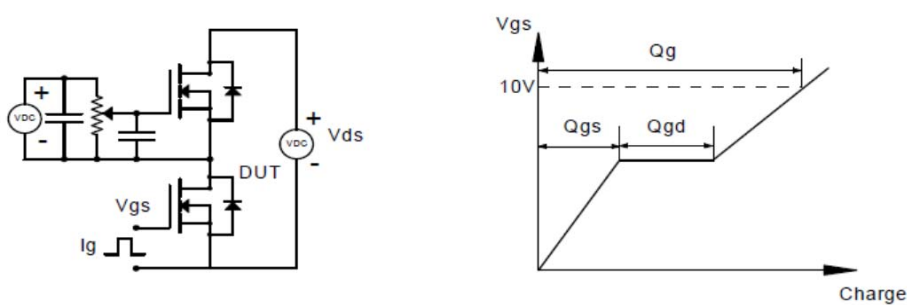
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

Kwansemi Semiconductor Co.,Ltd

Email:Sales@kwansemi.com

Web:www.kwansemi.com

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